

MJE180/181/182

Low Power Audio Amplifier Low Current High Speed Switching Applications



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------------|--|------------|-------|
| V _{CBO} | Collector-Base Voltage : MJE180 | 60 | V |
| | : MJE181 | 80 | V |
| | : MJE182 | 100 | V |
| V _{CEO} | Collector-Emitter Voltage : MJE180 | 40 | V |
| | : MJE181 | 60 | V |
| | : MJE182 | 80 | V |
| V _{EBO} | Emitter-Base Voltage | 7 | V |
| I _C | Collector Current (DC) | 3 | А |
| I _{CP} | Collector Current (Pulse) | 6 | А |
| I _B | Base Current | 1 | А |
| P _C | Collector Dissipation (T _a =25°C) | 1.5 | W |
| P _C | Collector Dissipation (T _C =25°C) | 12.5 | W |
| T _J | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | - 65 ~ 150 | °C |

Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Max. | Units |
|-----------------------|--------------------------------------|---|------|------|-------|
| BV _{CEO} | Collector -Emitter Breakdown Voltage | | | | |
| | : MJE180 | $I_C = 10 \text{mA}, I_B = 0$ | 40 | | V |
| | : MJE181 | | 60 | | V |
| | : MJE182 | | 80 | | V |
| I _{CBO} | Collector Cut-off Current : MJE180 | $V_{CB} = 60V, I_{B} = 0$ | | 0.1 | μΑ |
| | : MJE181 | $V_{CB} = 80V, I_{E} = 0$ | | 0.1 | μΑ |
| | : MJE182 | $V_{CB} = 100V, I_{E} = 0$ | | 0.1 | μΑ |
| | : MJE180 | $V_{CB} = 60V, I_{E} = 0 @ T_{C} = 150^{\circ}C$ | | 0.1 | mA |
| | : MJE181 | $V_{CB} = 80V, I_{E} = 0 @ T_{C} = 150^{\circ}C$ | | 0.1 | mA |
| | : MJE182 | $V_{CB} = 100V, I_{E} = 0 @ T_{C} = 150^{\circ}C$ | | 0.1 | mA |
| I _{EBO} | Emitter Cut-off Current | $V_{BE} = 7V, I_{C} = 0$ | | 0.1 | μΑ |
| h _{FE} | DC Current Gain | $V_{CE} = 1V, I_{C} = 100 \text{mA}$ | 50 | 250 | |
| | | $V_{CE} = 1V, I_{C} = 500mA$ | 30 | | |
| | | $V_{CE} = 1V, I_{C} = 1.5A$ | 12 | | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | $I_C = 500 \text{mA}, I_B = 50 \text{mA}$ | | 0.3 | V |
| | | $I_C = 1.5A, I_B = 150mA$ | | 0.9 | V |
| | | $I_C = 3A, I_B = 600mA$ | | 1.7 | V |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | $I_C = 1.5A, I_B = 150mA$ | | 1.5 | V |
| | | $I_C = 3A$, $I_B = 600mA$ | | 2.0 | V |
| V _{BE} (on) | Base-Emitter ON Voltage | V _{CE} = 1V, I _C = 500mA | | 1.2 | V |
| f _T | Current Gain Bandwidth Product | V _{CE} = 10V, I _C = 100mA | 50 | | MHz |
| C _{ob} | Output Capacitance | $V_{CB} = 10V, I_E = 0, f = 0.1MHz$ | | 30 | pF |

Typical Characteristics

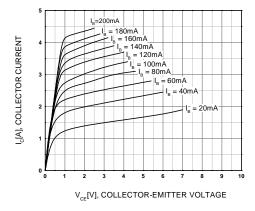


Figure 1. Static Characteristic

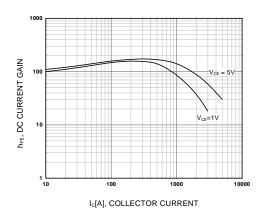


Figure 2. DC current Gain

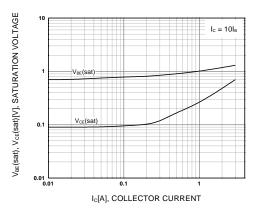


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

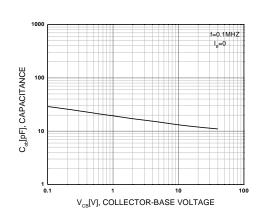


Figure 4. Collector Output Capacitance

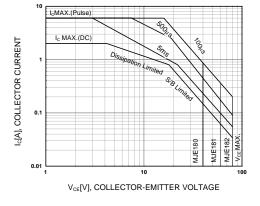


Figure 5. Safe Operating Area

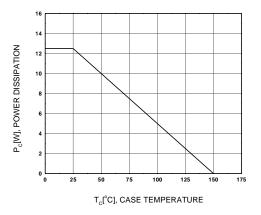
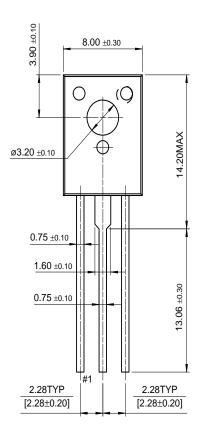


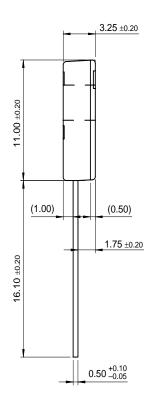
Figure 6. Power Derating

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Package Demensions

TO-126







Dimensions in Millimeters

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|---|--|---|---|
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